



Abstract:

The present invention relates to the use of a highly concentrated solution of one or more hafnium alkoxides as precursors for hafnium oxide and hafnium oxynitride layers. The present invention relates in particular to the use of a 30 to 90% strength by weight solution of one or more hafnium alkoxides for producing hafnium oxide and hafnium oxynitride layers for CVD or ALD methods. In addition, the invention relates to a process for the production of a hafnium oxide and hafnium oxynitride layer on an article to be coated, and a hafnium alkoxide solution which contains 30 to 90% by weight of one or more hafnium alkoxides. In a further embodiment of the invention, hafnium is replaced by zirconium in said compounds.

